

# SKM 75GB123D



SEMITRANS<sup>®</sup> 2

## IGBT Modules

SKM 75GB123D

SKM 75GAL123D

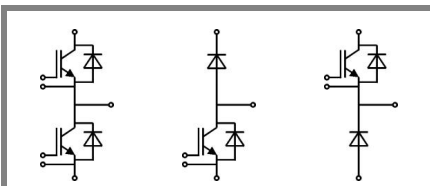
SKM 75GAR123D

### Features

- MOS input (voltage controlled)
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to  $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distance (20 mm)

### Typical Applications

- AC inverter drives
- UPS



GB

GAL

GAR

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200		V
$I_C$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75	A
		$T_{case} = 80^\circ\text{C}$	60	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	150		A
$V_{GES}$		$\pm 20$		V
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		$\mu\text{s}$
<b>Inverse Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75	A
		$T_{case} = 80^\circ\text{C}$	50	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	150		A
$I_{FSM}$	$t_p = 10\text{ ms}; \sin.$	$T_j = 150^\circ\text{C}$	480	A
<b>Freewheeling Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	95	A
		$T_{case} = 80^\circ\text{C}$	65	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200		A
$I_{FSM}$	$t_p = 10\text{ ms}; \sin$	$T_j = 150^\circ\text{C}$	720	A
<b>Module</b>				
$I_{t(RMS)}$		200		A
$T_{vj}$		- 40 ... + 150		$^\circ\text{C}$
$T_{stg}$		- 40 ... + 125		$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_c = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	4,5	5,5	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$		0,1	0,3	mA
$V_{CE0}$		$T_j = 25^\circ\text{C}$	1,4	1,6	V
		$T_j = 125^\circ\text{C}$	1,6	1,8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	22	28	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	30	38	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$		2,5	3	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	3,3		nF
$C_{oes}$			0,5		nF
$C_{res}$			0,22		nF
$Q_G$	$V_{GE} = -8 - +20\text{ V}$		500		nC
$R_{Gint}$	$T_j = ^\circ\text{C}$		5		$\Omega$
$t_{d(on)}$	$R_{Gon} = 22\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 50\text{ A}$	44	100	ns
$t_r$			56	100	ns
$E_{on}$	$R_{Goff} = 22\ \Omega$	$T_j = 125^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$	8		mJ
$t_{d(off)}$			380	500	ns
$t_f$			70	100	ns
$E_{off}$			5		mJ
$R_{th(j-c)}$	per IGBT		0,27		K/W



**SEMITRANS® 2**

## IGBT Modules

**SKM 75GB123D**

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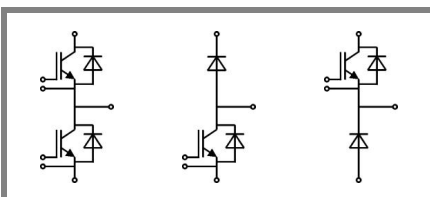
**SKM 75GAR123D**

### Features

- MOS input (voltage controlled)
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to  $6 \times I_{cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
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- Large clearance (10 mm) and creepage distance (20 mm)

### Typical Applications

- AC inverter drives
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Characteristics		min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,8		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$	18	26	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$			mΩ
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	35		A
$Q_{rr}$	$di/dt = 800 \text{ A}/\mu\text{s}$				μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)D}$	per diode			0,6	K/W
<b>Freewheeling Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,85	2,2	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,6		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$	15	20	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	40		A
$Q_{rr}$					μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)FD}$	per diode			0,5	K/W
<b>Module</b>					
$L_{CE}$				30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25 \text{ }^\circ\text{C}$	0,75		mΩ
		$T_{case} = 125 \text{ }^\circ\text{C}$	1		mΩ
$R_{th(c-s)}$	per module			0,05	K/W
$M_s$	to heat sink M6		3	5	Nm
$M_t$	to terminals M5		2,5	5	Nm
w				160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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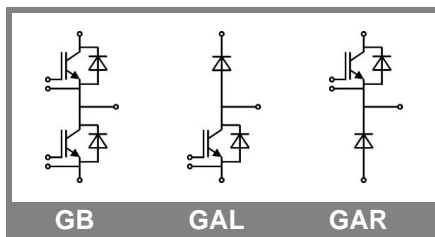
### Features

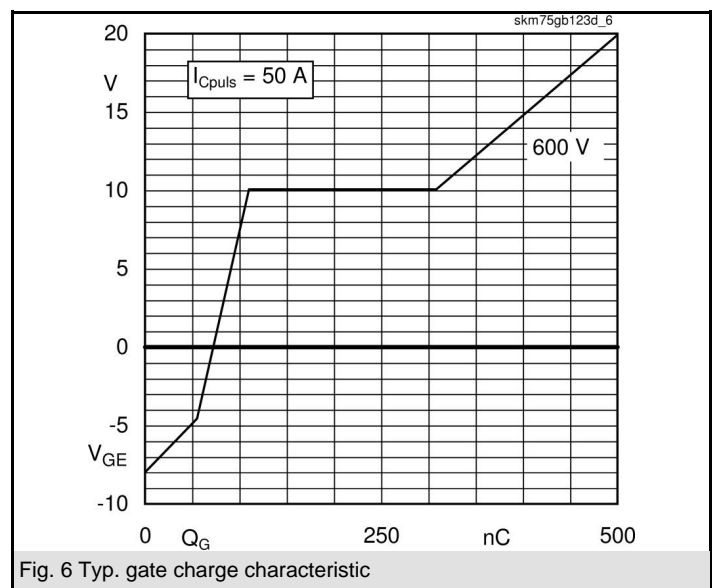
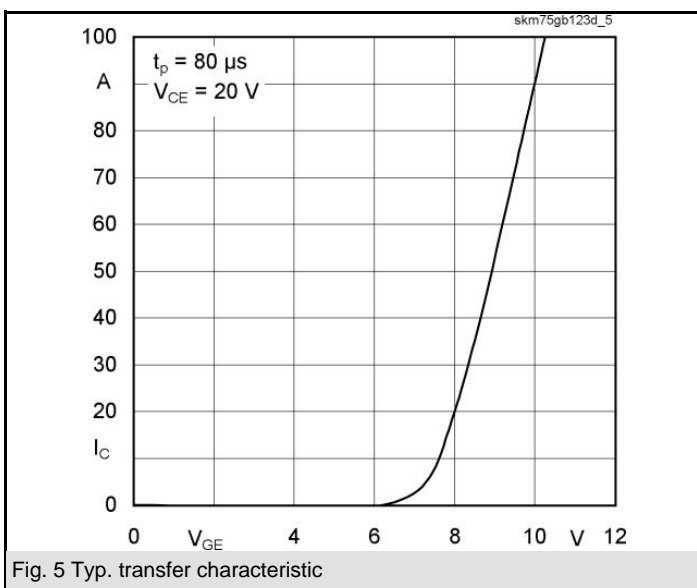
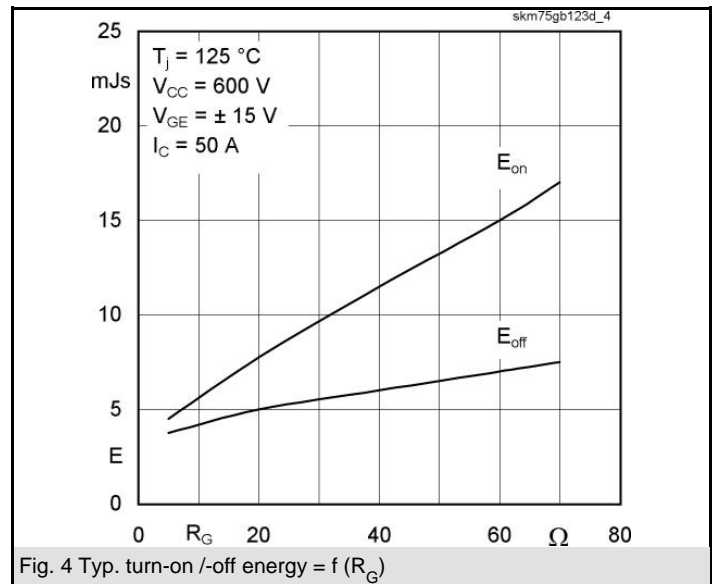
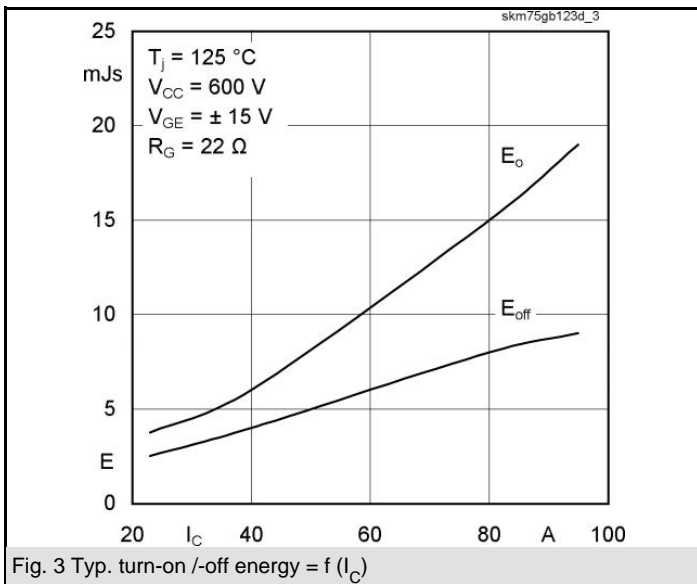
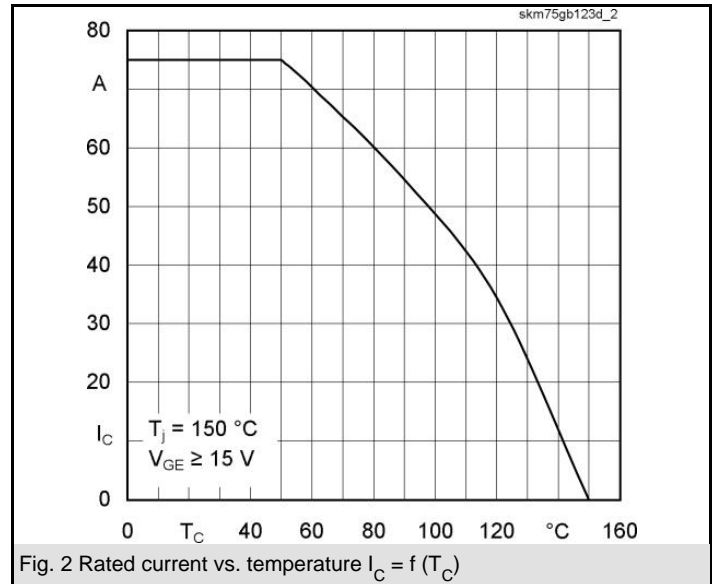
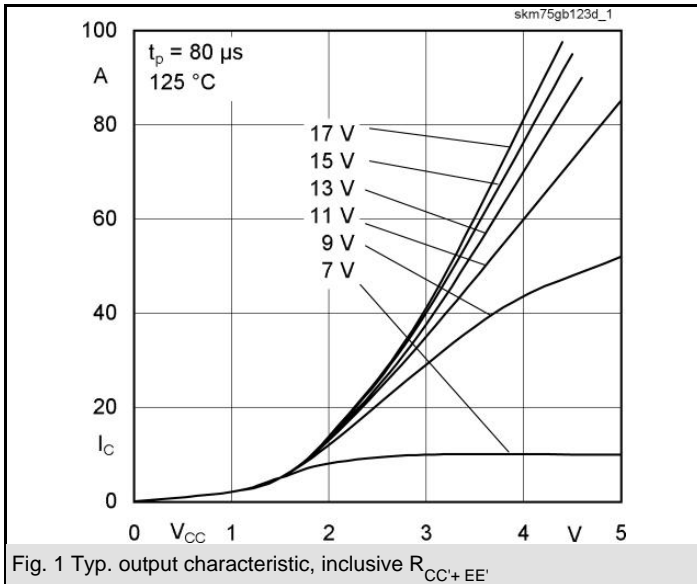
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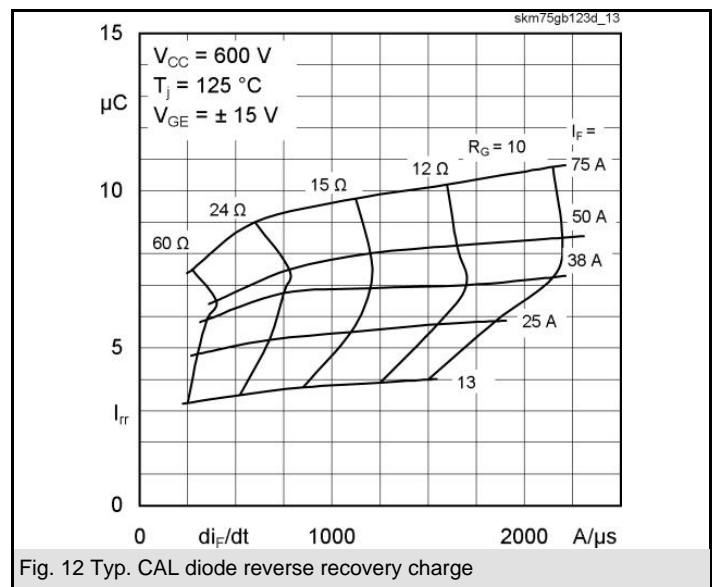
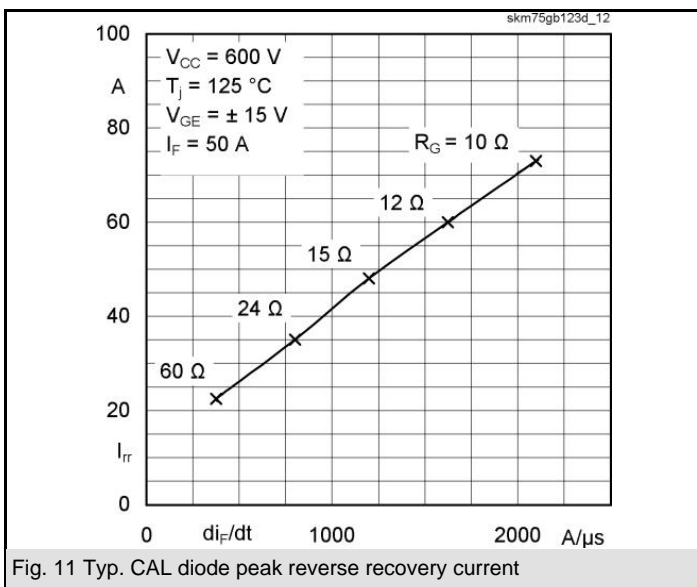
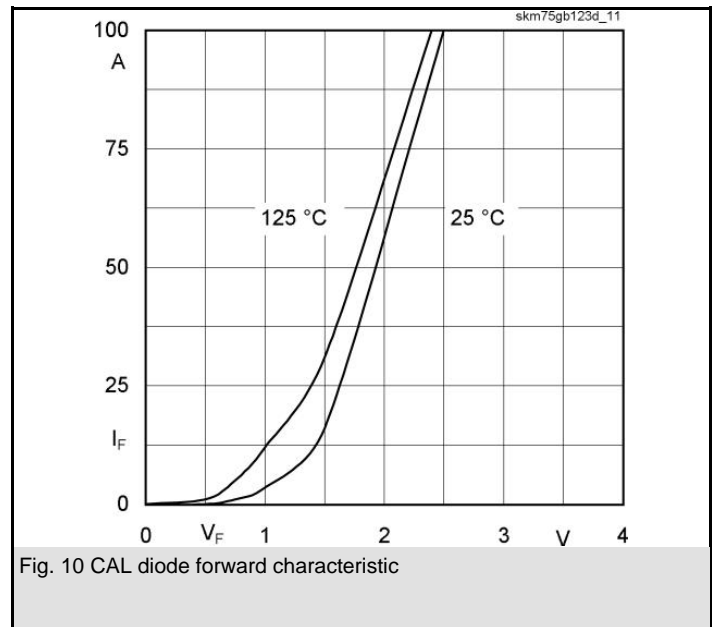
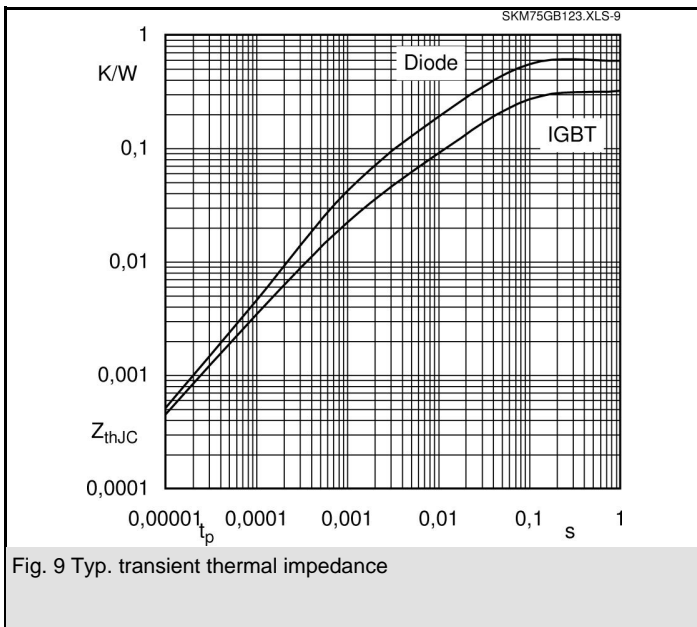
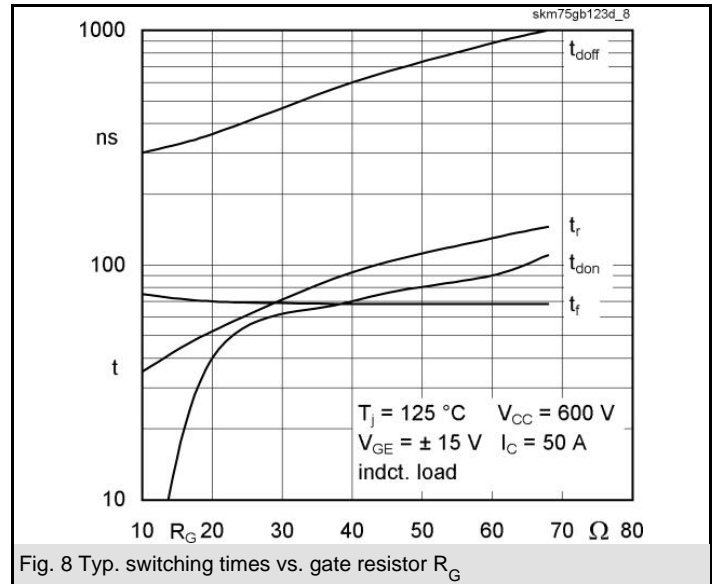
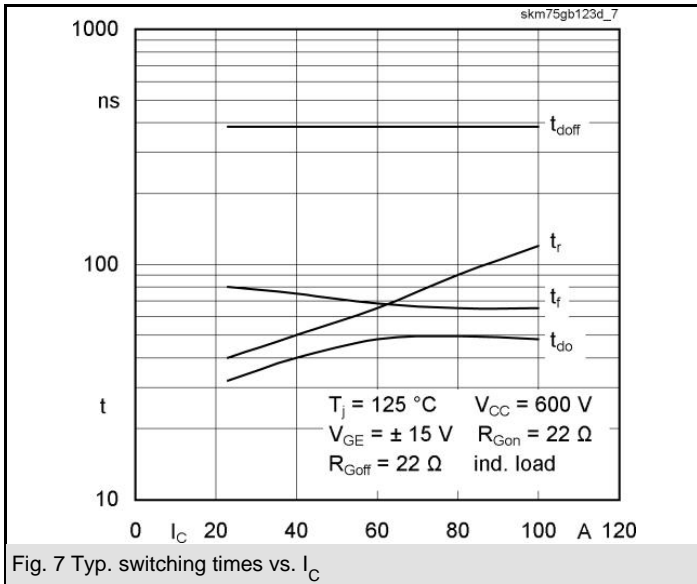
### Typical Applications

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- UPS

$Z_{th}$		Conditions	Values	Units
<b><math>Z_{th(j-c)I}</math></b>				
$R_{\theta j-c}$	$i = 1$		180	mk/W
$R_{\theta j-c}$	$i = 2$		64	mk/W
$R_{\theta j-c}$	$i = 3$		22	mk/W
$R_{\theta j-c}$	$i = 4$		4	mk/W
$\tau_{th(j-c)}$	$i = 1$		0,0327	s
$\tau_{th(j-c)}$	$i = 2$		0,0479	s
$\tau_{th(j-c)}$	$i = 3$		0,008	s
$\tau_{th(j-c)}$	$i = 4$		0,005	s
<b><math>Z_{th(j-c)D}</math></b>				
$R_{\theta j-cD}$	$i = 1$		380	mk/W
$R_{\theta j-cD}$	$i = 2$		190	mk/W
$R_{\theta j-cD}$	$i = 3$		26	mk/W
$R_{\theta j-cD}$	$i = 4$		4	mk/W
$\tau_{th(j-c)D}$	$i = 1$		0,0947	s
$\tau_{th(j-c)D}$	$i = 2$		0,006	s
$\tau_{th(j-c)D}$	$i = 3$		0,08	s
$\tau_{th(j-c)D}$	$i = 4$		0,003	s







# SKM 75GB123D

UL Recognized

CASED61

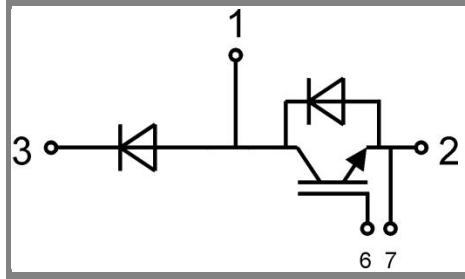
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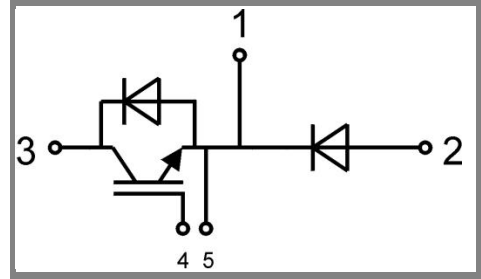
Case D 61



GB Case D 61



GAL Case D 62 (→ D 61)



GAR Case D 63 (→ D 61)